



STP12NK60Z STF12NK60Z, STW12NK60Z

N-channel 650 V @Tjmax, 0.53 Ω , 10 A TO-220, TO-220FP, TO-247
Zener-protected SuperMESH™ Power MOSFET

Features

Type	V _{DSS} (@Tjmax)	R _{DS(on)} max	I _D	P _W
STP12NK60Z	650 V	<0.640 Ω	10 A	150 W
STF12NK60Z	650 V	<0.640 Ω	10 A	35 W
STW12NK60Z	650 V	<0.640 Ω	10 A	150 W

- Extremely high dv/dt capability
- 100% avalanche tested
- Gate charge minimized
- Very low intrinsic capacitances
- Very good manufacturing repeatability

Application

- Switching applications

Description

The SuperMESH™ series is obtained through an extreme optimization of ST's well established strip-based PowerMESH™ layout. In addition to pushing on-resistance significantly down, specialties is taken to ensure a very good dv/dt capability for the most demanding application. Such series complements ST full range of high voltage Power MOSFETs.

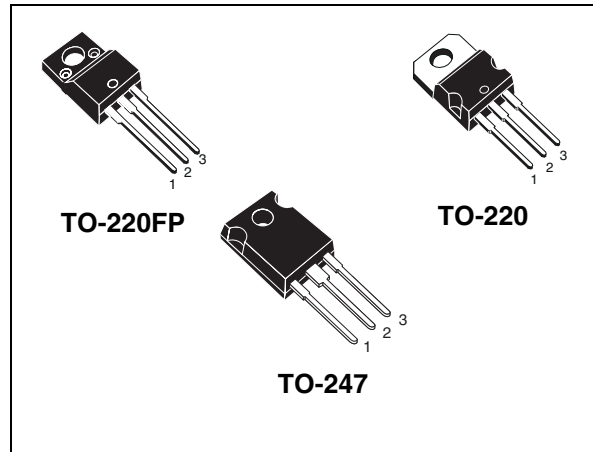


Figure 1. Internal schematic diagram

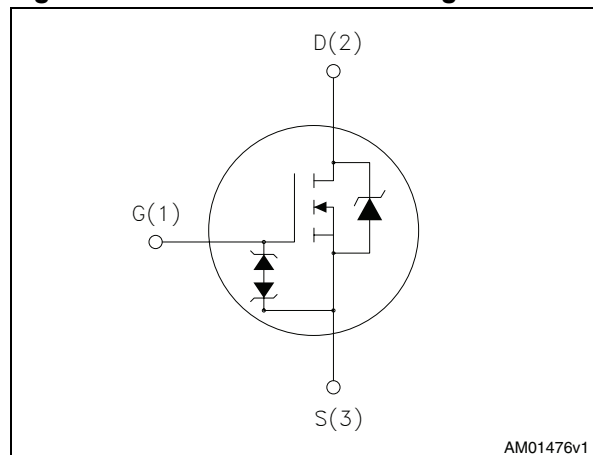


Table 1. Device summary

Order codes	Marking	Package	Packaging
STP12NK60Z	P12NK60Z	TO-220	Tube
STF12NK60Z	F12NK60Z	TO-220FP	Tube
STW12NK60Z	W12NK60Z	TO-247	Tube

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		TO-220, TO-247	TO-220FP	
V_{DS}	Drain-source voltage ($V_{GS} = 0$)	600		V
V_{GS}	Gate-source voltage	± 30		V
I_D	Drain current (continuous) at $T_C = 25\text{ }^{\circ}\text{C}$	10	10 ⁽¹⁾	A
I_D	Drain current (continuous) at $T_C = 100\text{ }^{\circ}\text{C}$	6.3	6.3 ⁽¹⁾	A
I_{DM} ⁽²⁾	Drain current (pulsed)	40	40 ⁽¹⁾	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^{\circ}\text{C}$	150	35	W
	Derating factor	1.2	0.27	W/ $^{\circ}\text{C}$
$V_{ESD(G-S)}$	Gate source ESD (HBM-C=100 pF, R=1.5 k Ω)		2500	V
dv/dt ⁽³⁾	Peak diode recovery voltage slope	4.5		V/ns
V_{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink ($t = 1\text{ s}$; $T_C = 25\text{ }^{\circ}\text{C}$)		2500	V
T_{stg}	Storage temperature	-55 to 150		$^{\circ}\text{C}$
T_j	Max operating junction temperature	150		$^{\circ}\text{C}$

1. Limited only by maximum temperature allowed

2. Pulse width limited by safe operating area

3. $I_{SD} \leq 10\text{ A}$, $di/dt \leq 200\text{ A}/\mu\text{s}$, $V_{DD} = 480\text{ V}$

Table 3. Thermal data

Symbol	Parameter	Value			Unit
		TO-220	TO-247	TO-220FP	
$R_{thj-case}$	Thermal resistance junction-case max	0.83		3.6	$^{\circ}\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-ambient max	62.5	50	62.5	$^{\circ}\text{C}/\text{W}$
T_l	Maximum lead temperature for soldering purpose	300			$^{\circ}\text{C}$

Table 4. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AS}	Avalanche current, repetitive or not-repetitive (pulse width limited by T_j Max)	10	A
E_{AS}	Single pulse avalanche energy (starting $T_j = 25\text{ }^{\circ}\text{C}$, $I_D = I_{AS}$, $V_{DD} = 50\text{ V}$)	260	mJ

2 Electrical characteristics

($T_{CASE} = 25\text{ °C}$ unless otherwise specified)

Table 5. On/off

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$, $V_{GS} = 0$	600			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{Max rating}$ $V_{DS} = \text{Max rating}$, $T_C = 125\text{ °C}$			1 50	μA μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{ V}$			± 10	μA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 100\text{ }\mu\text{A}$	3	3.75	4.5	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}$, $I_D = 5\text{ A}$		0.53	0.64	Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS} = 10\text{ V}$, $I_D = 5\text{ A}$	-	9	-	S
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$	-	1740 195 49	-	pF pF pF
$C_{oss\text{ eq.}}^{(2)}$	Equivalent output capacitance	$V_{GS} = 0$, $V_{DS} = 0\text{ to }480\text{ V}$	-	101	-	pF
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	Turn-on delay time Rise time Turn-off delay time Fall time	$V_{DD} = 300\text{ V}$, $I_D = 5\text{ A}$, $R_G = 4.7\text{ }\Omega$ $V_{GS} = 10\text{ V}$ (see Figure 19)	-	22.5 18.5 55 31.5	-	ns ns ns ns
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 480\text{ V}$, $I_D = 10\text{ A}$, $V_{GS} = 10\text{ V}$ (see Figure 20)	-	59 10 32	-	nC nC nC

1. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2. $C_{oss\text{ eq.}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DS}

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
I_{SD}	Source-drain current		-		10	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		40	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 10\text{ A}$, $V_{GS} = 0$	-		1.6	V
t_{rr}	Reverse recovery time	$I_{SD} = 10\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$	-	358		ns
Q_{rr}	Reverse recovery charge	$V_{DD} = 50\text{ V}$	-	3		μC
I_{RRM}	Reverse recovery current	(see Figure 24)	-	17		A
t_{rr}	Reverse recovery time	$I_{SD} = 10\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$	-	460		ns
Q_{rr}	Reverse recovery charge	$V_{DD} = 50\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$	-	4.2		μC
I_{RRM}	Reverse recovery current	(see Figure 24)	-	18.2		A

1. Pulse width limited by safe operating area

2. Pulsed: Pulse duration = 300 μs , duty cycle 1.5%

Table 8. Gate-source Zener diode

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
$BV_{GSO}^{(1)}$	Gate-Source breakdown voltage	$I_{GS} = \pm 1\text{ mA}$ (open drain)	30	-	-	V

1. The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for TO-220

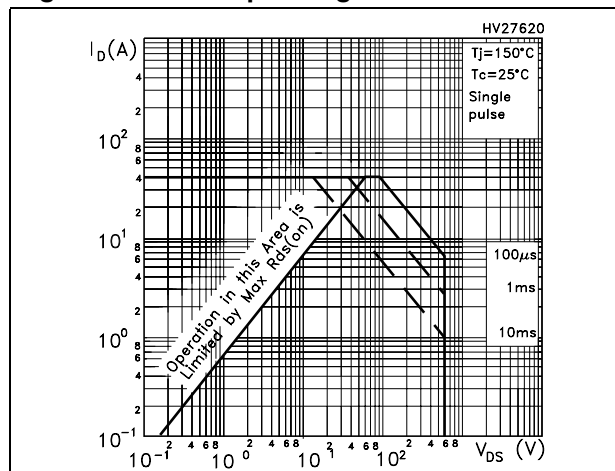


Figure 3. Thermal impedance for TO-220

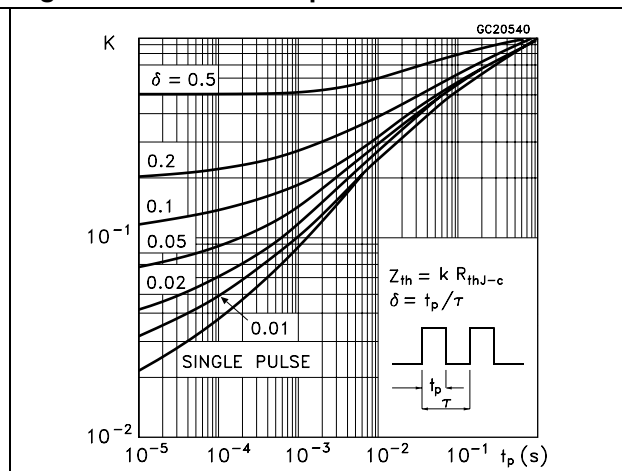


Figure 4. Safe operating area for TO-247

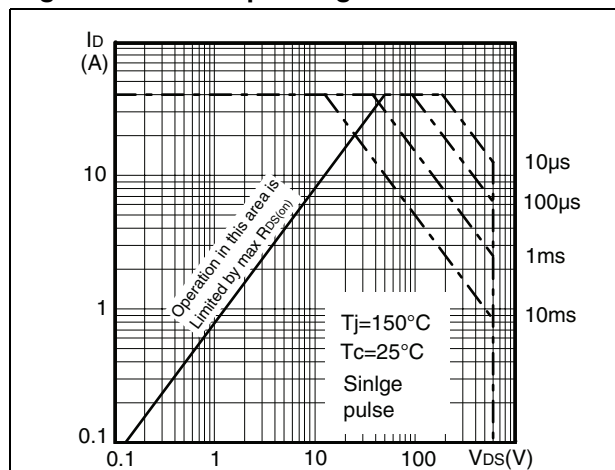


Figure 5. Thermal impedance for TO-247

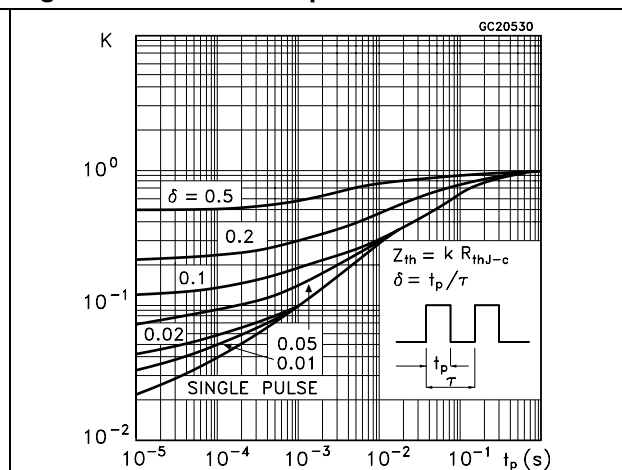


Figure 6. Safe operating area for TO-220FP

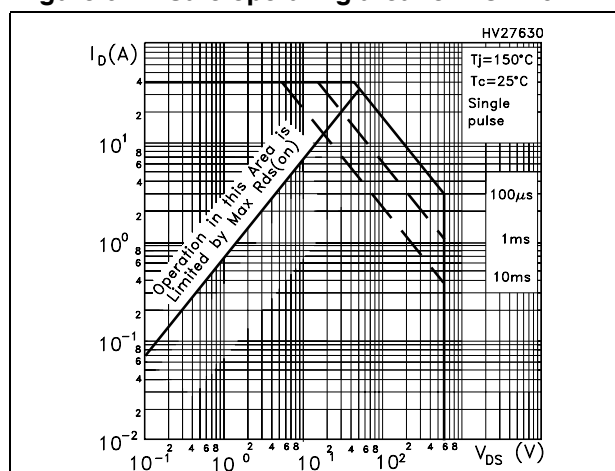


Figure 7. Thermal impedance for TO-220FP

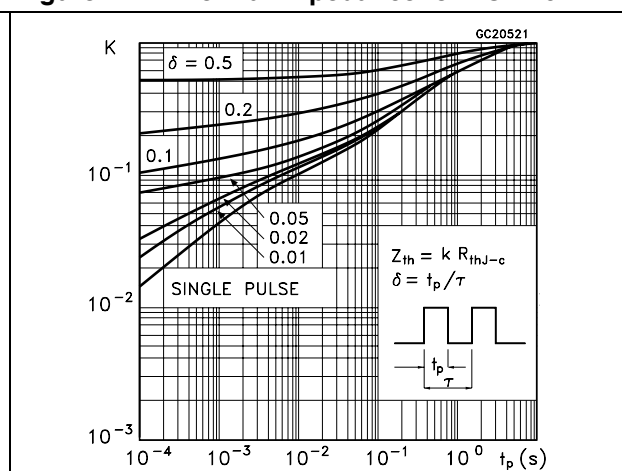


Figure 8. Output characteristics

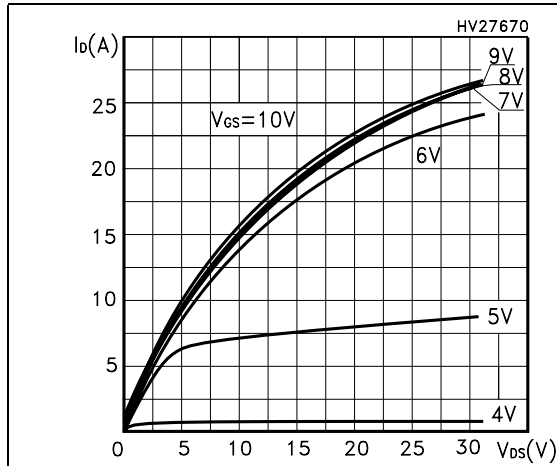


Figure 9. Transfer characteristics

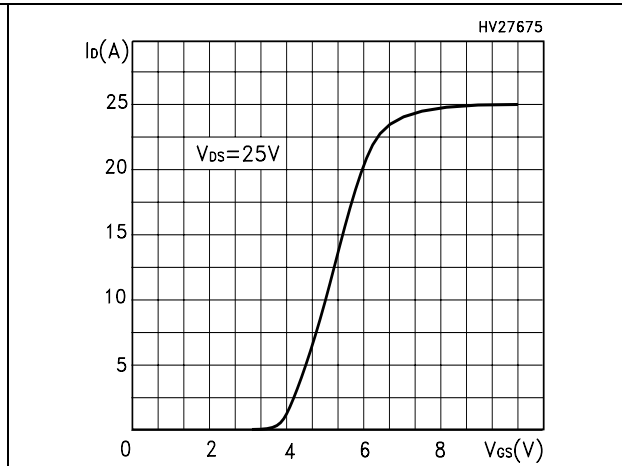


Figure 10. Transconductance

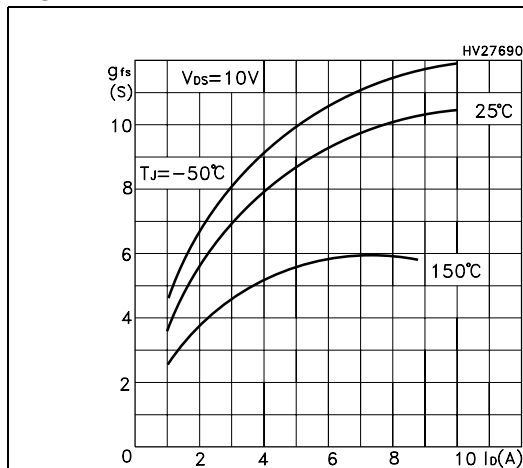


Figure 11. Static drain-source on resistance

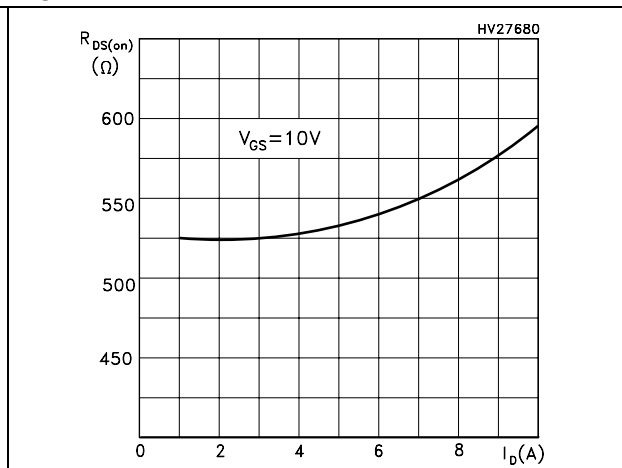


Figure 12. Gate charge vs gate-source voltage

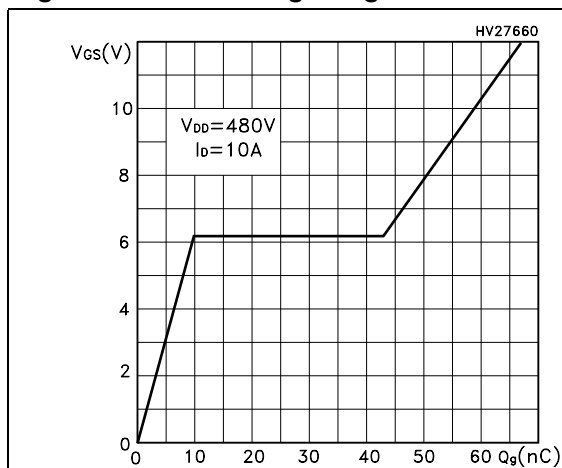


Figure 13. Capacitance variations

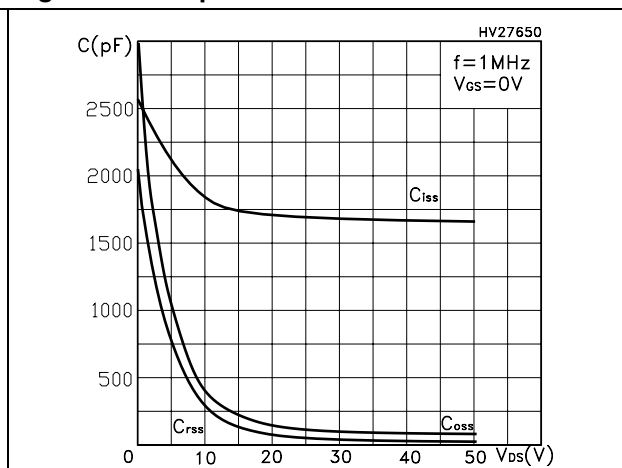


Figure 14. Normalized gate threshold voltage vs temperature

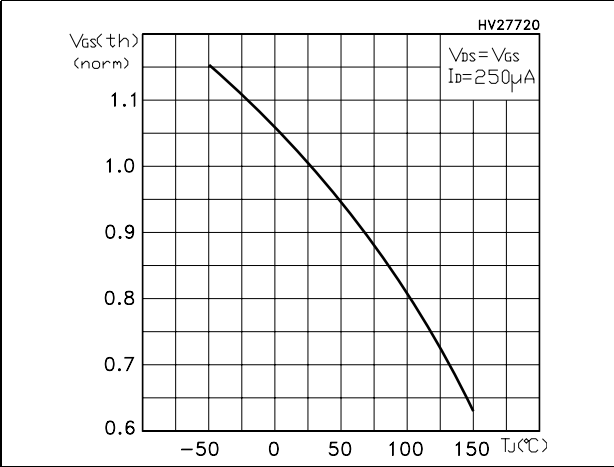


Figure 15. Normalized on resistance vs temperature

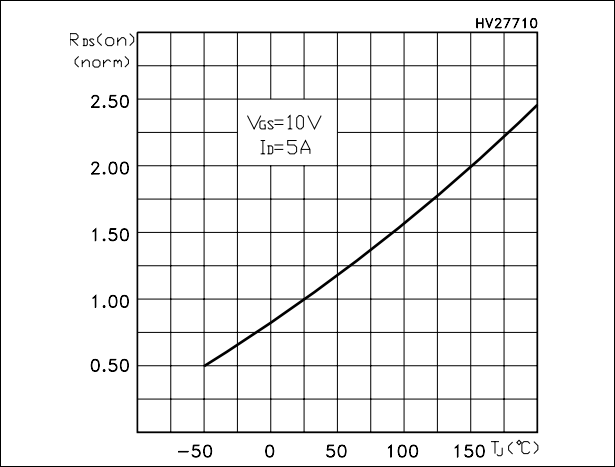


Figure 16. Source-drain diode forward characteristics

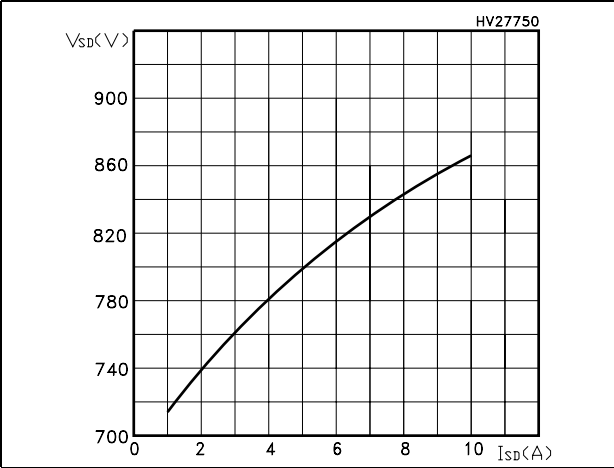


Figure 17. Normalized breakdown voltage vs temperature

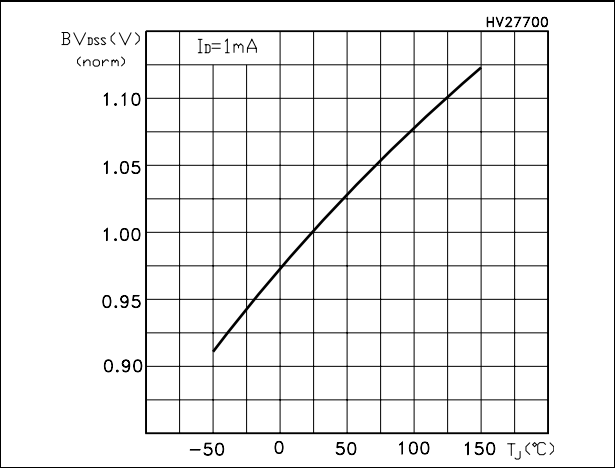
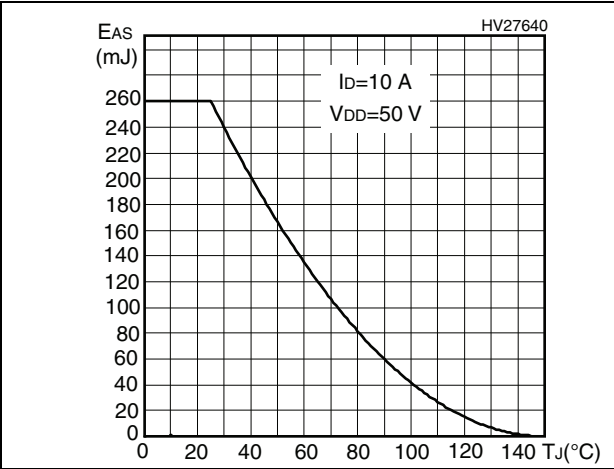


Figure 18. Maximum avalanche energy vs temperature



3 Test circuits

Figure 19. Switching times test circuit for resistive load

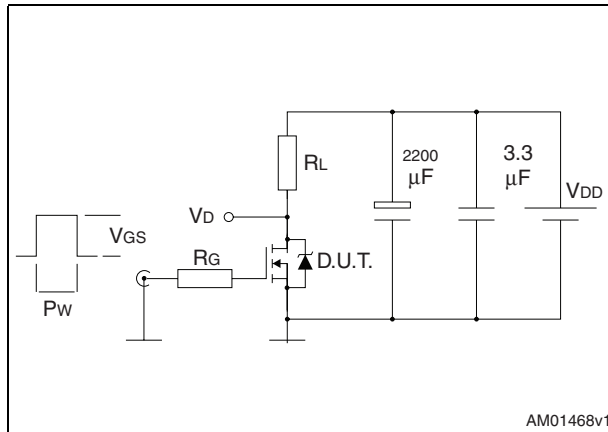


Figure 20. Gate charge test circuit

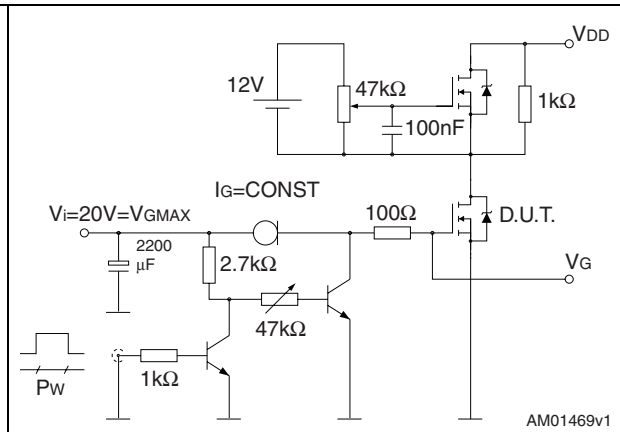


Figure 21. Test circuit for inductive load switching and diode recovery times

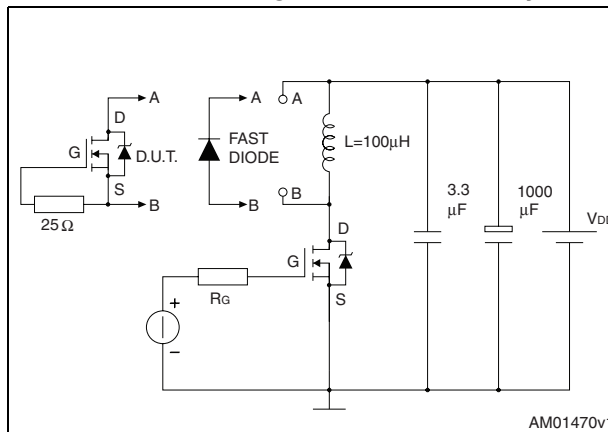


Figure 22. Unclamped inductive load test circuit

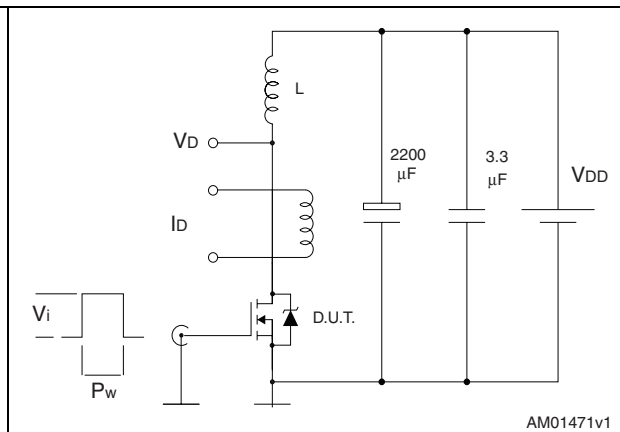


Figure 23. Unclamped inductive waveform

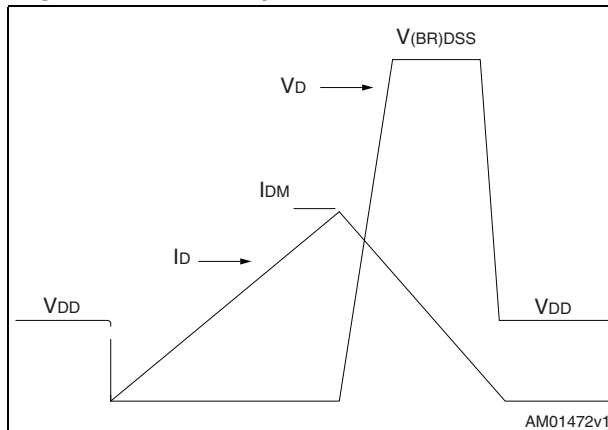
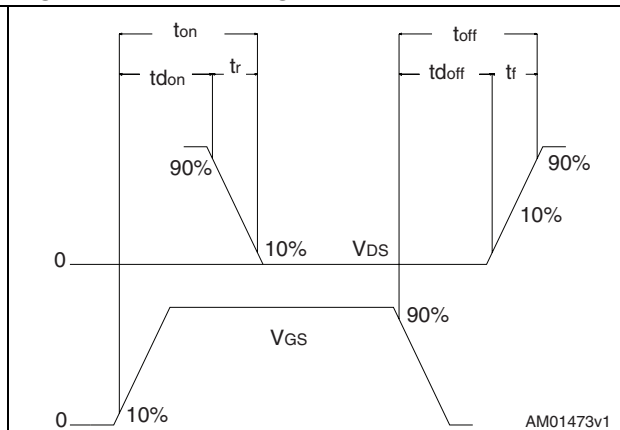


Figure 24. Switching time waveform

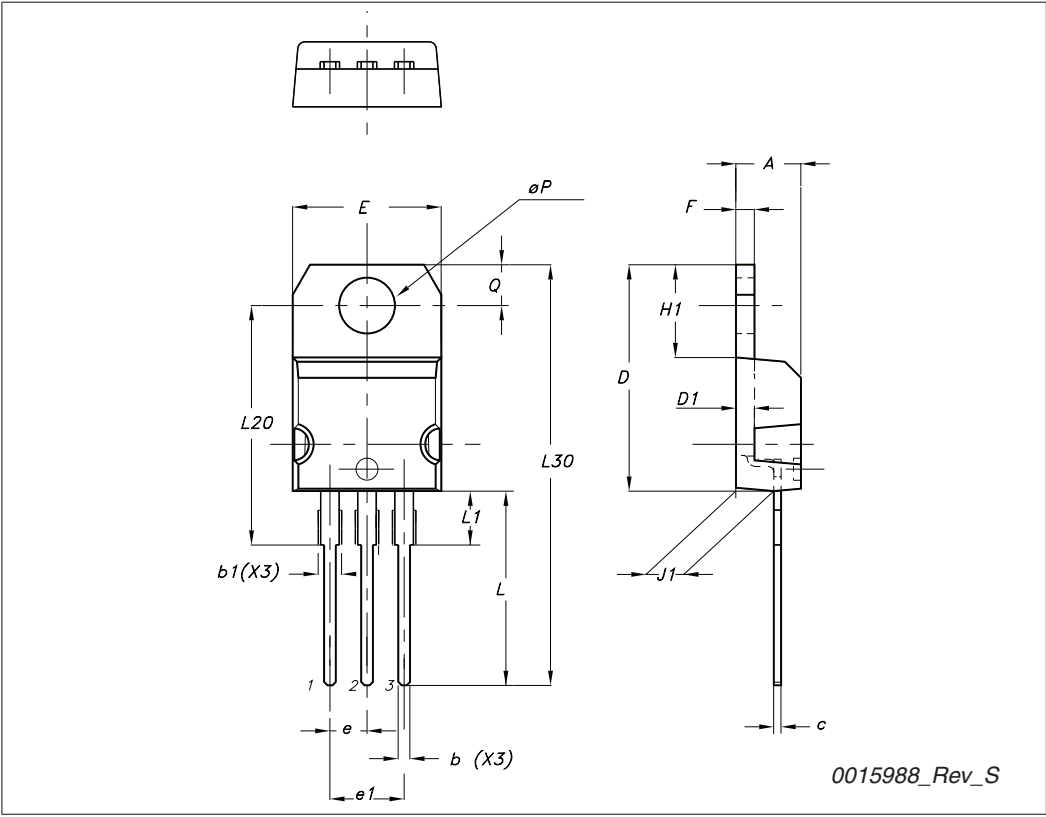


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

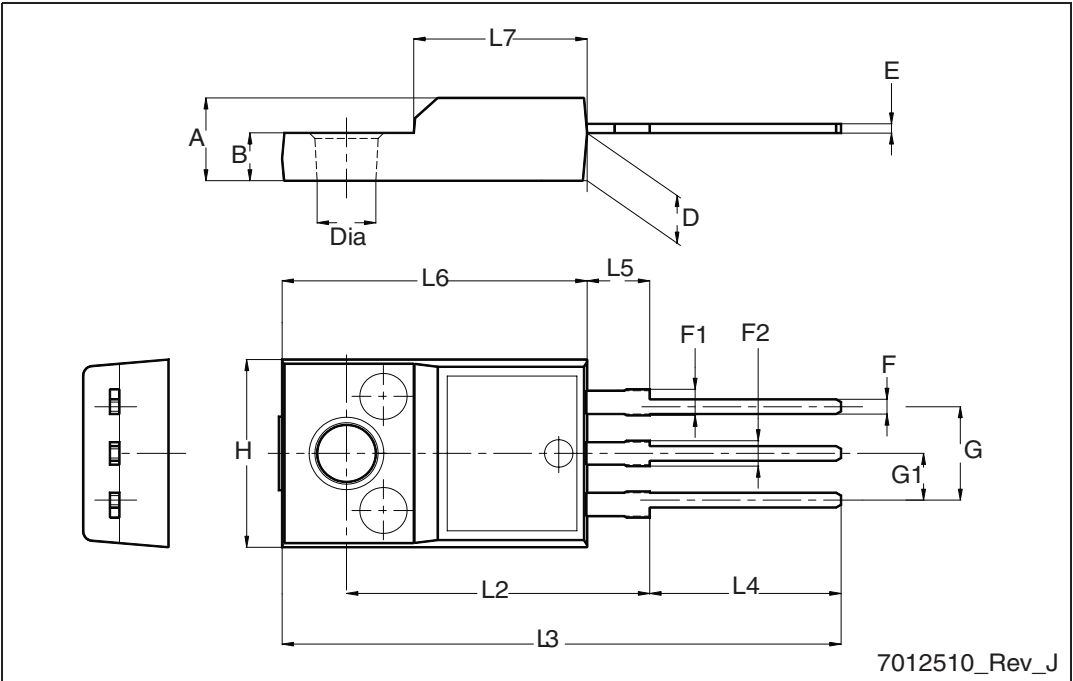
TO-220 type A mechanical data

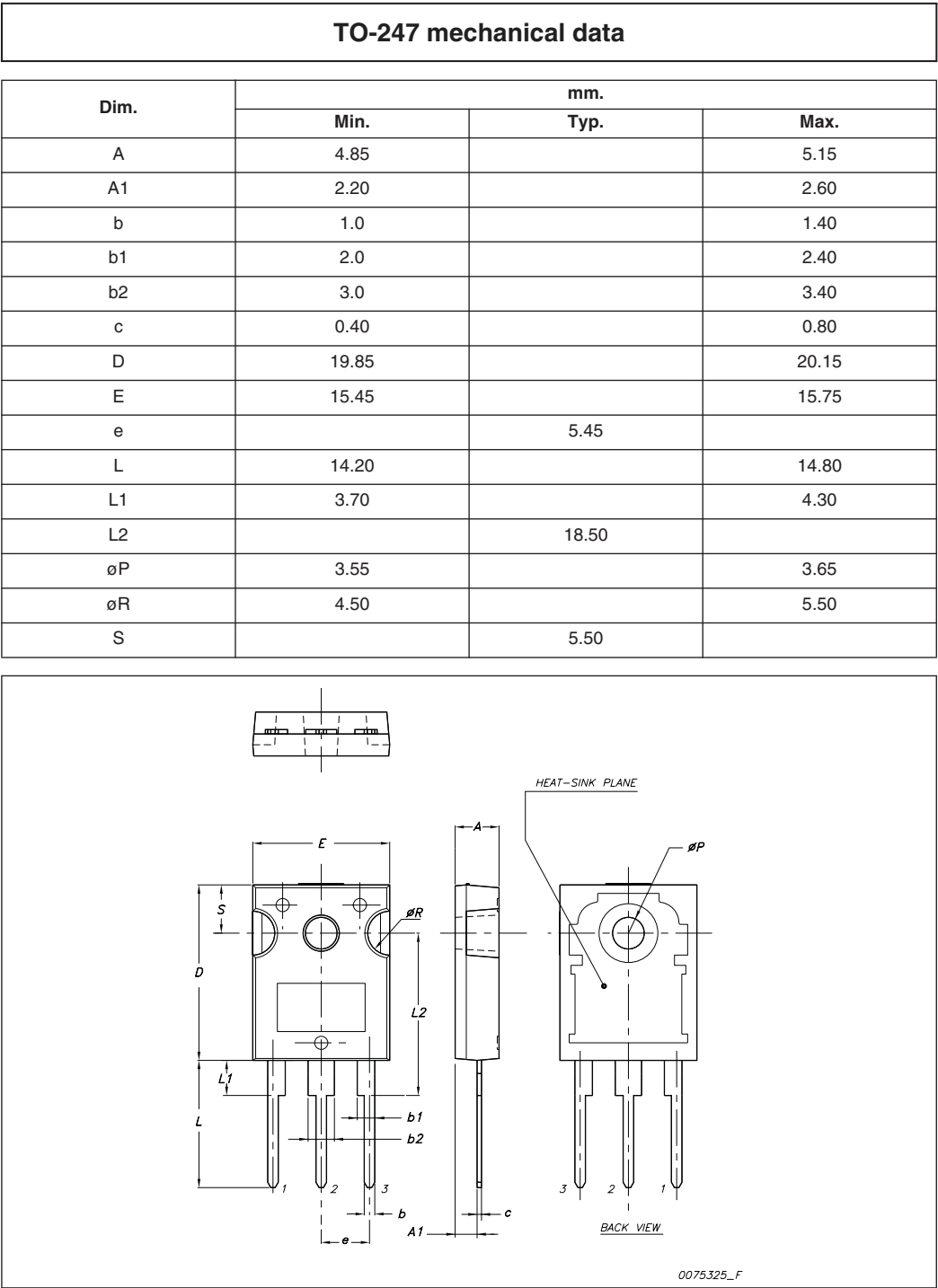
Dim	mm		
	Min	Typ	Max
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95



TO-220FP mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.5
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2





5 Revision history

Table 9. Document revision history

Date	Revision	Changes
12-Apr-2004	1	First release
06-Sep-2005	2	Inserted ecopack indication
13-Sep-2005	3	Final version
05-Sep-2006	4	The document has been reformatted
26-Apr-2007	5	The document has been updated on 1: Electrical ratings
25-Jan-2008	6	Modified: dv/dt value on Table 2: Absolute maximum ratings
13-Oct-2009	7	Added new package, mechanical data: TO-247

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